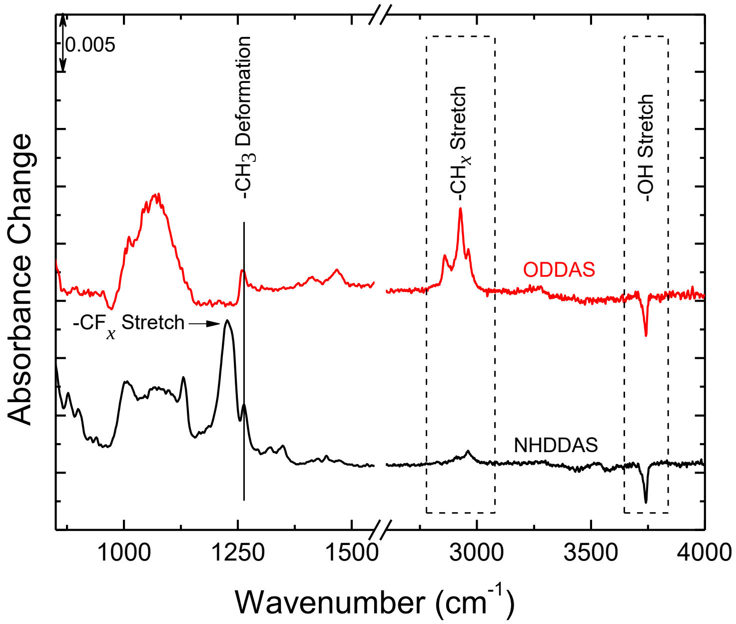

Figure 1. Infrared absorbance change of inhibitors on SiO_2 through vapor phase method at a substrate temperature of 200 °C.

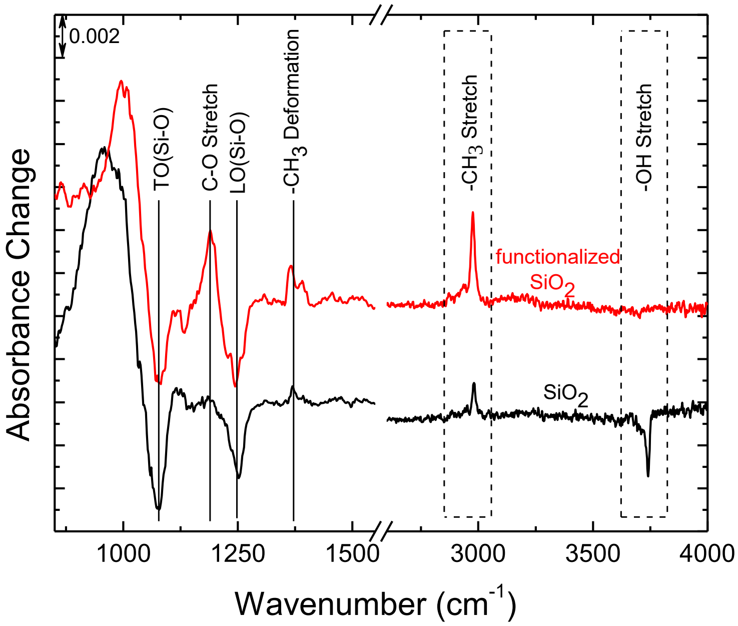

Figure 2. Infrared absorbance change during the reaction of ZTB with pristine SiO_2 and functionalized SiO_2 at a substrate temperature of 200 °C, respectively.